May 2014



FQA13N50CF

# N-Channel QFET® FRFET® MOSFET

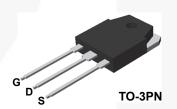
500 V, 15 A, 480 mΩ

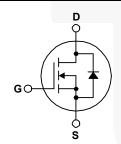
### **Features**

- 15 A, 500 V,  $R_{DS(on)}$  = 480 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 7.5 A
- Low Gate Charge (Typ. 43 nC)
- Low C<sub>rss</sub> (Typ. 20 pF)
- 100% Avalanche Tested
- Fast Recovery Body Diode (Typ. 100 ns)

## **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQA13N50CF	Unit
V <sub>DSS</sub>	Drain-Source Voltage		500	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		15	Α
	- Continuous (T <sub>C</sub> = 100°C)		9.5	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	60	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy		860	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	15	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	21.8	mJ
dv/dt	Peak Diode Recovery dv/dt		4.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		218	W
	- Derate above 25°C		1.56	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8""from case for 5 seconds		300	°C

### **Thermal Characteristics**

Symbol	Parameter	FQA13N50CF	Unit	
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.58	°C/W	
$R_{ heta JS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA13N50CF	FQA13N50CF	TO-3PN	Tube	N/A	N/A	30 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Charac	teristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V, } I_{D} = 250  \mu\text{A}$	500			V
ΔBV <sub>DSS</sub> / ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.5		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V			1	μΑ
		V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Charact	teristics					•
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.5A		0.43	0.48	Ω
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 7.5 \text{ A}$	\	15		S
Dynamic Cl	haracteristics			1	ı	
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$	\	1580	2055	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz	\	180	235	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			20	25	pF
Switching C	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 250 V, I <sub>D</sub> = 15A,		25	60	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		100	210	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			130	270	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		100	210	ns
Qg	Total Gate Charge	$V_{DS} = 400 \text{ V}, I_{D} = 15\text{A},$	/	43	56	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V	/	7.5		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	-/	18.5		nC
Drain-Source	ce Diode Characteristics and Maximum Ratings			1		
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				15	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				60	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 15 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 15 A,		100		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$		0.4		μС

#### NOTES

<sup>1.</sup> Repetitive rating: pulse-width limited by maximum junction temperature.

<sup>2.</sup> L = 5.6 mH, I<sub>AS</sub> = 15 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.

 $<sup>3.</sup>I_{SD} \leq 15$  A, di/dt  $\leq 200$  A/µs,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J$  = 25°C.

<sup>4.</sup> Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

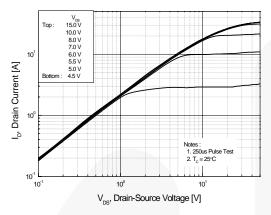
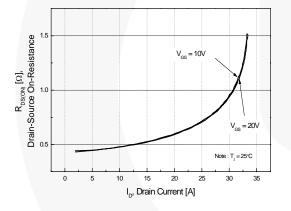


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage



**Figure 5. Capacitance Characteristics** 

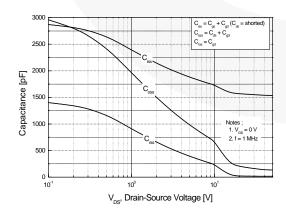


Figure 2. Transfer Characteristics

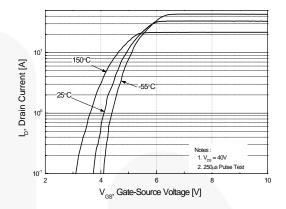


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

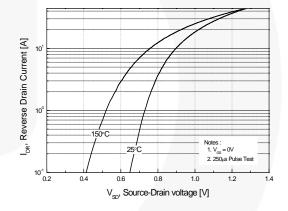
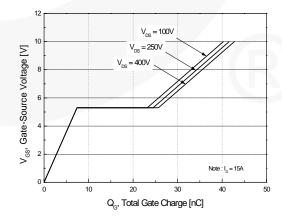


Figure 6. Gate Charge Characteristics



## Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

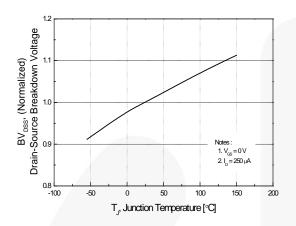


Figure 8. On-Resistance Variation vs. Temperature

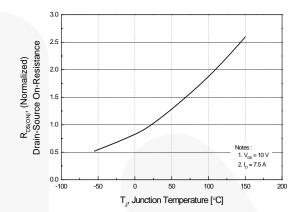


Figure 9. Maximum Safe Operating Area

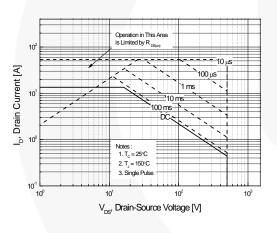


Figure 10. Maximum Drain Current vs. Case Temperature

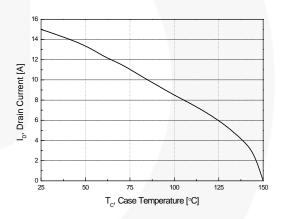
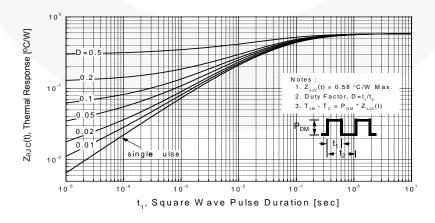


Figure 11. Transient Thermal Response Curve



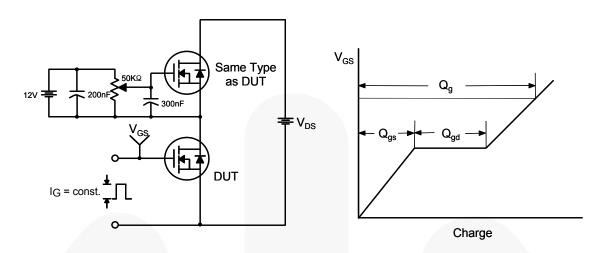


Figure 12. Gate Charge Test Circuit & Waveform

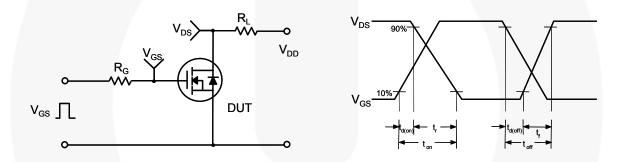


Figure 13. Resistive Switching Test Circuit & Waveforms

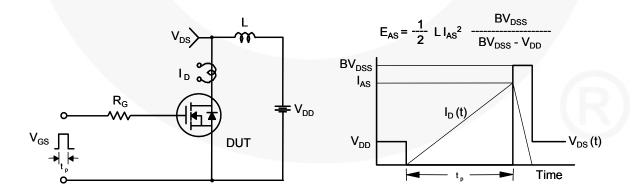


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

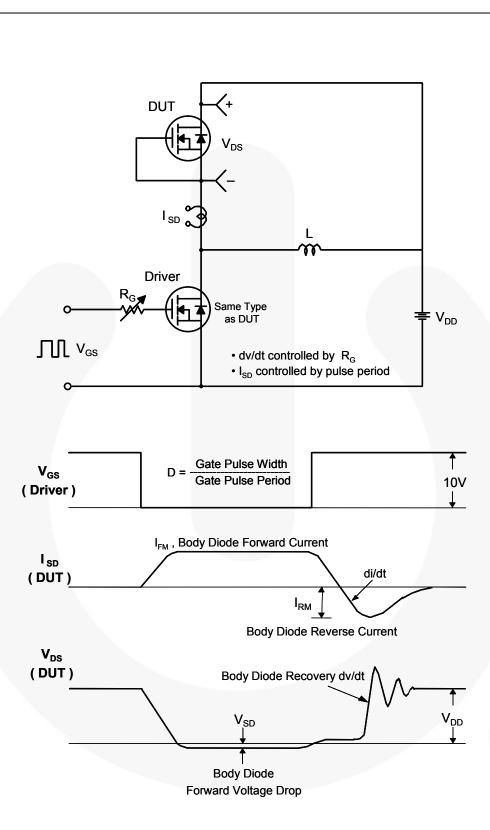
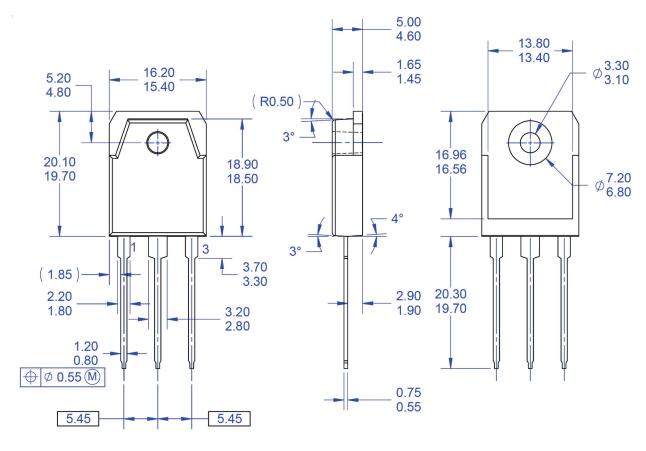
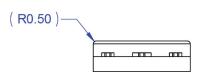


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

### **Mechanical Dimensions**





#### NOTES: UNLESS OTHERWISE SPECIFIED

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   B) ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5-2009. D) DIMENSIONS ARE EXCLUSSIVE OF BURRS,
- MOLD FLASH, AND TIE BAR EXTRUSSIONS.
  E) DRAWING FILE NAME: TO3PN03AREV1.
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### Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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